

Expertise Applied | Answers Delivered

Residential **Solar Solutions**



Renewable Energy



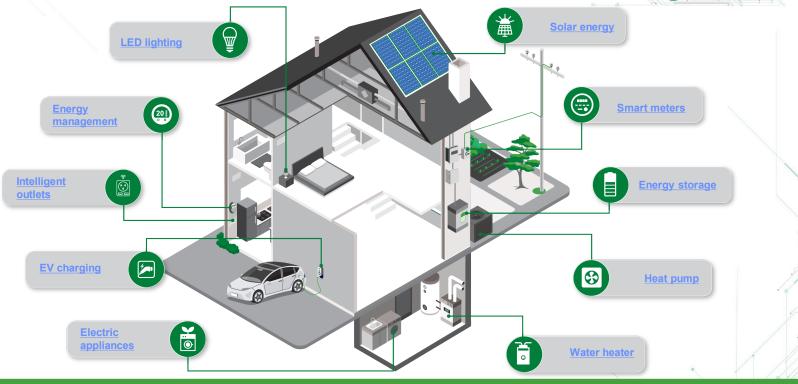
Building Solutions

Users must independently evaluate the suitability of and test each product selected for their own specific applications. It is the User's sole responsibility to determine fitness for a particular system or use based on their own performance criteria, conditions, specific application, compatibility with other parts, and environmental conditions. Users must independently provide appropriate design and operating safeguards to minimize any risks associated with their applications and products. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at littelfuse.com/disclaimer-electronics.

RFV1023

Solar power and energy storage is the key to "net-zero" homes and residential buildings





Littelfuse technologies are helping drive decarbonization in clean energy systems.



Types of solar inverters for residential applications

Micro inverter



Features

- Panel-level DC to AC conversion
- Single phase; rated up to 300 W range; output voltage 110-230 V
- Power output of each panel is optimized independently
- Easily expandable systems to meet future needs
- Battery back-up AC coupled

Power optimizer + string inverter



Features

- Centralized DC to AC conversion
- Rated up to 300 W range; output voltage 50 VDC (per panel)
- Power output of each panel is optimized independently
- Provide both system- and panel-level monitoring
- Battery back-up can be high-voltage DC coupled

String inverter



Features

- Centralized DC to AC conversion
- Rated 1 kW-10 kW; output voltage: single-phase 230 V and three-phase 400 V
- Easier system maintenance with no electronics on the roof
- Known for their availability and reliability
- Battery back-up can be high-voltage DC coupled



Residential solar inverter market is growing at CAGR of 11%

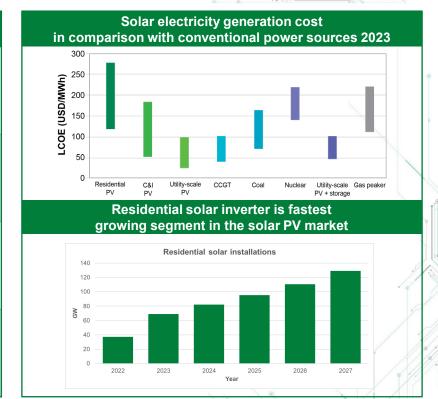
Market trends and drivers

Both the rooftop and utility-scale segments experienced strong growth in 2022. The energy crisis played a role, and the reaction from citizens was immediate: the rooftop market increased by 50% in 2022, with installations reaching 118 GW from 79 GW the year before.

The impressive growth of the rooftop segment was seen across the world in 2022 - Brazil added an additional 5.3 GW, Italy 127%, Spain 105%, and China 51.1 GW (54% of it's 2022 installations.)

In 2023, the rooftop segment is expected to further increase to 159 GW, a 35% growth from 2022. We expect a slight slowdown in the growth rate of the rooftop segment in the following years, as energy prices are expected to return to lower levels. The annual installed rooftop capacity is forecasted to increase to 183 GW in 2024 and up to 268 GW in 2027.

Solar panels are becoming integral building materials, and smart cities are embracing small-scale distributed solar panels combined with storage and digital solutions.





Source

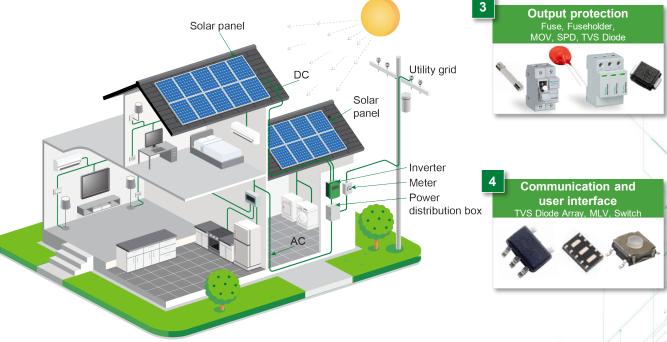
- 1. Residential Solar PV Inverter Market
- 2. PV Inverter Market Size

- 3. iea.org
- 4. Global Market Outlook 2023-2027

Littelfuse recommended solutions for residential solar inverters

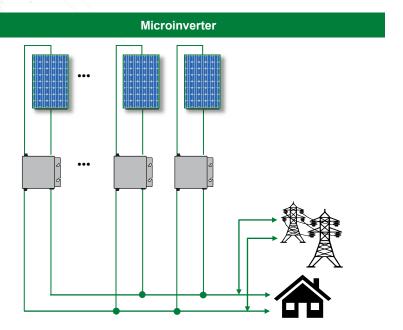


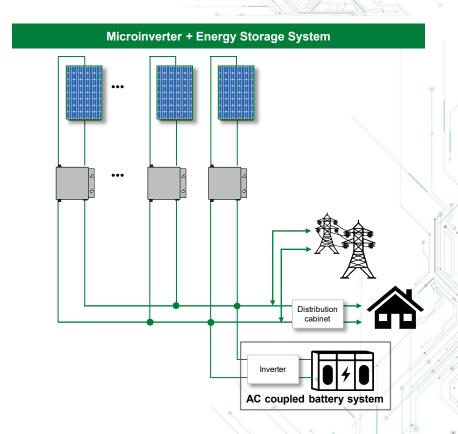






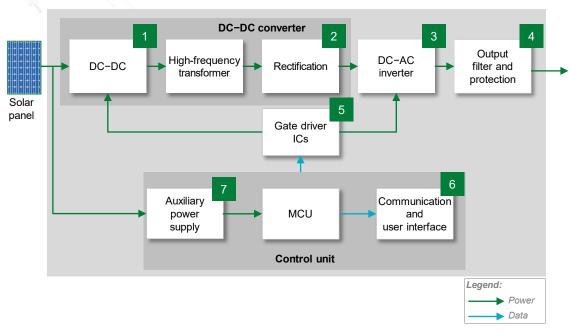
Microinverter topologies







Microinverter block diagram



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	Technology	Product series
	MOSFET	Trench Gate Gen2, X4-Class
1	TVS Diode	SMCJ, SMDJ
	NTC	RA, RB, KR
2	SiC Schottky Diode	650V Diodes
	MOSFET or	Ultra-junction X2, X4-Class
3	IGBT	650 V Trench
	TVS Diode	<u>SMBJ</u>
	MOV	TMOV, UltraMOV, LA
4	GDT	<u>CG3/CG4</u>
	Fuse	<u>215</u> , <u>369</u>
_	Gate Driver	IXD_6xxSI
5	TVS Diode	<u>SMBJ</u>
6	TVS Diode Array	<u>SP712,</u> <u>SP2555NUTG</u>
7	MOSFET	650V X2-Class, 650V X3-Class

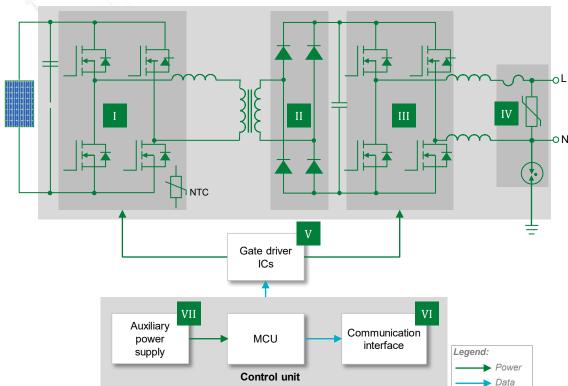


Recommended Littelfuse products for microinverters

	Technology	Function in application	Series	Benefits	Features
	MOSFET	High-frequency switching	Trench Gate Gen2, X4-Class	High power density; easy to mount; space-saving	Ultra low on-resistance R _{DS} ; high current handling capability; fast body diode
1	TVS Diode	Protects MOSFET from voltage transients	SMCJ, SMDJ	Enables compact design; improves system reliability	3000 W P _{PPM} capability; low profile package
	NTC	High temperature detection due to high sunlight, power component failure, etc.	RA, RB, KR	Provides safe operation of PV panels; smaller footprint saves space	Surface mountable; small form factor
2	SiC Schottky Diodes	Used for rectification	650V Diodes	Reduces switching losses; increases system efficiency, reliability, and thermal management	High surge capability; negligible reverse recovery current; T_j = 175 $^{\circ}$ C
	MOSFET or	Convert DC voltage from PV panel to AC	Ultra-junction X2, X4-Class	High efficiency; high power density; easy to mount	Ultra low on-resistance R _{DS(ON)} and gate charge Qg; low package inductance; dv/dt ruggedness
3	IGBT	line voltage	650 V Trench	Reduced thermal resistance; low energy losses; fast switching	Low V_{sat} , low E_{on}/E_{off} , high surge current capability; positive thermal co-efficient of $V_{CE(sat)}$
	TVS Diode	Protects IGBTs from transient overload event	<u>SMBJ</u>	Enables compact design; improves system reliability	600 W peak pulse power capability; excellent clamping capability; small footprint
	MOV	Protects power unit from voltage transients and lightning	TMOV, UltraMOV, LA	Reduces customer qualification time by complying with third-party safety standards	High energy absorption capability: 40-530 J (2 ms)
4	GDT	Protects from voltage transients and lightning	<u>CG3/CG4</u>	Small form-factor allows compact system design; enables product to comply with IEC/UL standards	High energy absorption capability; small form-factor; low leakage current
	Fuse	Protects from overcurrent events	<u>215</u> , <u>369</u>	Reduces customer qualification time by complying with third-party safety standards	High breaking capacity; meets the IEC 60127-2
5	Gate Driver	Controls the switching MOSFETs	IXD 6xxSI	Dual outputs provide space-efficient design; high immunity to latch-up; rise/fall times <10 ns	Tight tolerance; small form factor; fast thermal response
5	TVS Diode	Protects gate driver from transient overload event	<u>SMBJ</u>	Enables compact design; improves system reliability	600 W peak pulse power capability; excellent clamping capability; small footprint
6	TVS Diode Array	Protects data lines from ESD/EFT and surge events	<u>SP712,</u> <u>SP2555NUTG</u>	Minimizes signal distortion; reduces voltage over-shoot, and simplified PCB design	Low capacitance of 2.5 pF; low leakage current of 0.1 μ A; small form factor
7	MOSFET	High-frequency switching	650V X2-Class, 650V X3-Class	High power density; easy to mount; space-saving	Ultra-low on-resistance RDS; high current handling capability; fast body diode



Typical schematic of a microinverter

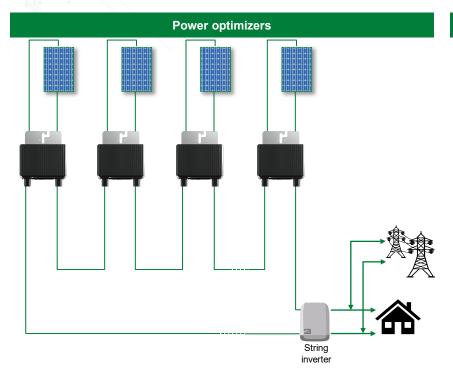


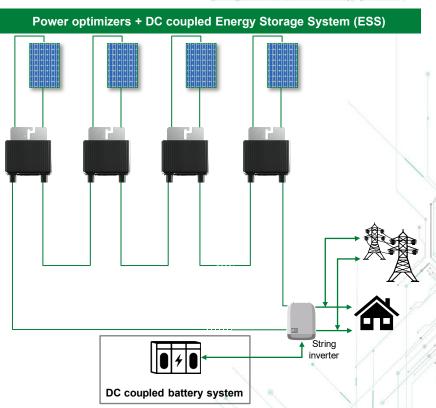
	Technology	Product series
	MOSFET	Trench Gate Gen2, X4-Class
I	TVS Diode	SMCJ, SMDJ
	NTC	<u>RA, RB, KR</u>
II	SiC Schottky Diode	650V Diodes
	MOSFET or IGBT	Ultra-junction X2, X4-Class
III		650 V Trench
	TVS Diode	<u>SMBJ</u>
	MOV	TMOV, UltraMOV, LA
IV	GDT	<u>CG3/CG4</u>
	Fuse	<u>215,</u> <u>369</u>
v	Gate Driver	IXD_6xxSI
V	TVS Diode	<u>SMBJ</u>
VI	TVS Diode Array	<u>SP712</u> <u>SP2555NUTG</u>
VII	MOSFET	650V X2-Class, 650V X3-Class



Power optimizer topologies

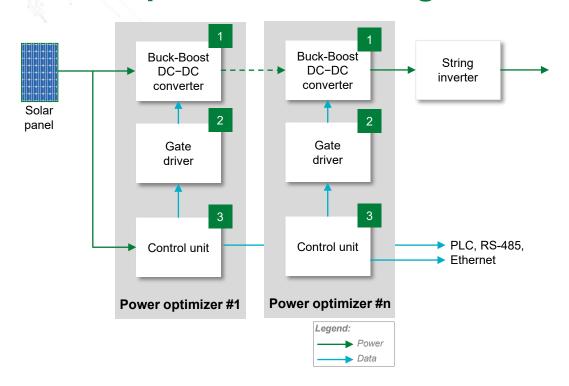
(Power optimizers may not be included in all string inverter-based PV systems)







Power optimizer block diagram



	Technology	Product series
	MOSFET	Trench Gate Gen2, X4-Class
1	TVS Diode	SMCJ, SMDJ, 1.5SMC
	NTC	RA, RB, KR
2	Gate Driver	IXD_6xxSI
2	TVS Diode	<u>SMBJ</u>
3	TVS Diode Array	<u>SP712, SP2555NUTG,</u> <u>SM712, SP3130</u>



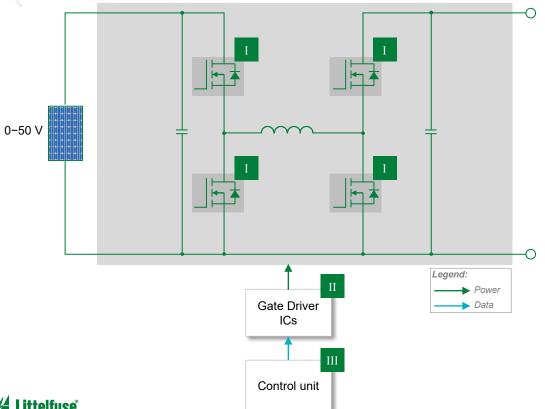
Recommended Littelfuse products for power optimizers

	Technology	Function in application	Series	Benefits	Features
	MOSFET	High-frequency switching	Trench Gate Gen2, X4-Class	High power density; easy to mount; space-saving	Ultra-low on-resistance RDS; high current handling capability; fast body diode
1	TVS Diode	Protects MOSFET from voltage transients	SMCJ, SMDJ, 1.5SMC	Enables compact design; improves system reliability	3000 W P _{PPM} capability; low-profile package
	NTC	High temperature detection due to high sunlight, power component failure, etc.	RA, RB, KR	Provides safer operation of PV panels; smaller footprint saves space	Surface mountable; small form factor
2	Gate Driver	Controls the switching MOSFETs	IXD_6xxSI	Dual outputs provide space-efficient design; high immunity to latch-up; rise/fall times <10 ns	Tight tolerance; small form factor; fast thermal response
2	TVS Diode	Protects gate driver from transient overload event	SMBJ	Enables compact design; improves system reliability	600 W peak pulse power capability; excellent clamping capability; small footprint
3	TVS Diode Array	Protects against ESD and EFT	SP712, SP2555NUTG, SM712, SP3130	Smaller form factor and multi-line protection enables ease of design	Low capacitance of 1.0 pF per I/O



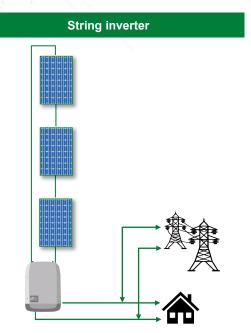


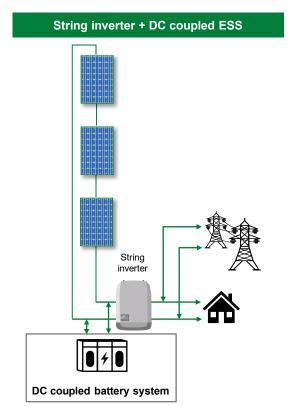
Typical schematic of a power optimizer

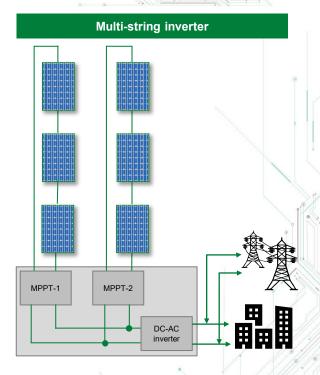


	Technology	Product series
	MOSFET	Trench Gate Gen2, X4-Class
I	TVS Diode	SMCJ, SMDJ, 1.5SMC
	NTC	<u>RA</u> , <u>RB</u> , <u>KR</u>
TT	Gate Driver	IXD_6xxSI
II	TVS Diode	<u>SMBJ</u>
III	TVS Diode Array	<u>SP712, SP2555NUTG,</u> <u>SM712, SP3130</u>

String inverter topologies

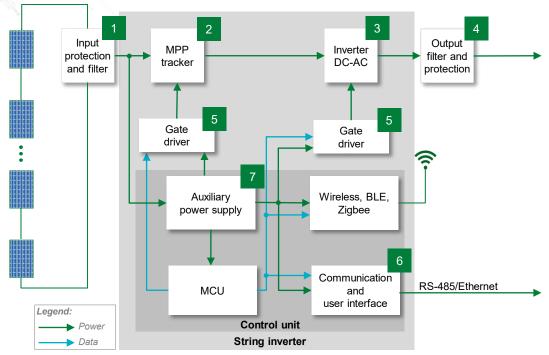








String inverter block diagram



	Technology	Product series
1	MOV	<u>UltraMOV, LA, SM20</u>
	MOSFET	650V X2-Class, 650V X3-Class
2	TVS Diode	SMCJ, SMDJ
_	SiC Schottky Diode	650V Diodes
	NTC	RA, RB, KR
	MOSFET or IGBT	650V X2-Class, 650V X3-Class
3	IGBT	650 V Trench
	TVS Diode	SMBJ
	MOV	TMOV, UltraMOV, LA
4	GDT	CG3/CG4
	Fuse	Class J, Class RK5, KLKD
5	Gate Driver	IXD_6xxSI, IX4351NE
3	TVS Diode	SMBJ
6	TVS Diode Array	<u>SP712, SM712</u> <u>SP2555NUTG</u>
	Switch	7000, <u>KSC</u> , <u>ES</u> , <u>KSR</u>
7	MOSFET	650V X2-Class, 650V X3-Class



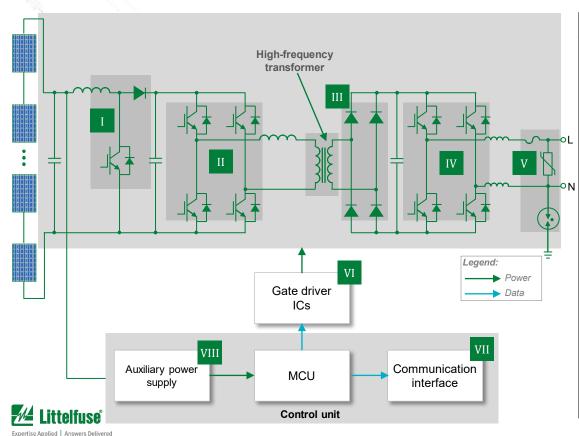
Recommended Littelfuse products for string inverters

	Technology	Function in application	Series	Benefits	Features
1	MOV	Protects from voltage transients and lighting surges	UltraMOV, LA, SM20	Reduces customer qualification time by complying with third-party safety standards	High energy absorption capability: 40–530 J (2 ms)
	MOSFET	High-frequency switching	650V X2-Class, 650V X3-Class	High power density; easy to mount; space-saving	Ultra-low on-resistance RDS; high current handling capability; fast body diode
	TVS Diode	Protects MOSFET from voltage transients	SMCJ, SMDJ	Enables compact design; improves system reliability	3000 W P _{PPM} capability; low profile package
2	SiC Schottky Diode	Used for rectification	650V Diodes	Reduces switching losses; increases system efficiency, reliability, and thermal management	High surge capability; negligible reverse recovery current; Tj = 175 °C
	NTC	High temperature detection due to high sunlight, power component failure, etc.	<u>RA, RB, KR</u>	Provides safe operation of PV panels; smaller footprint saves space	Surface mountable; small form factor
	MOSFET or	Converts DC voltage from PV panel to AC	650V X2-Class, 650V X3-Class	High efficiency; high power density; easy to mount	Ultra low on-resistance R _{DS(ON)} and gate charge Qg; low package inductance; dv/dt ruggedness
3	IGBT	line voltage	650 V Trench	Reduces thermal resistance; low energy losses; fast switching	Low V _{sat} , low E _{on} /E _{off} , high surge current capability; positive thermal coefficient of V _{CE(sat)}
	TVS Diode	Protects IGBTs from transient overload event	<u>SMBJ</u>	Enables compact design; improves system reliability	600 W peak pulse power capability; excellent clamping capability; small footprint
	MOV	Protects power lines from voltage transients and lightning surges	TMOV, UltraMOV, LA	Reduces customer qualification time by complying with third-party safety standards	High energy absorption capability: 40-530 J (2 ms)
4	GDT	Protects from voltage transients and lightning	<u>CG3/CG4</u>	Small form-factor allows for compact system design; enables product to comply with IEC/UL standards	High energy absorption capability; small form-factor; low leakage current
	Fuse	Protects from overcurrent events	Class J, Class RK5, KLKD	Reduces customer qualification time by complying with third-party safety standards	High breaking capacity; meets the IEC 60127-2
_	Gate Driver	Controls the switching MOSFETs	IXD_6xxSI, IX4351NE	Dual outputs provide space-efficient design; high immunity to latch-up; rise/fall times less than 10 ns	Tight tolerance; small form factor; fast thermal response
5	TVS Diode	Protects gate driver from transient overload event	<u>SMBJ</u>	Enables compact design; improves system reliability	600 W peak pulse power capability; excellent clamping capability; small footprint
6	TVS Diode Array	Protects data lines from ESD/EFT and surge events	<u>SP712, SM712</u> <u>SP2555NUTG</u>	Minimizes signal distortion; reduces voltage over-shoot; simplified PCB design	Low capacitance of 2.5 pF; low leakage current of 0.1 µA; small form factor
	Switch	On/Off/Reset switch	7000, KSC, ES, KSR	Micro miniature; long life; low voltage; low power and performance; low voltage leakage	IP 67 sealing; Au plating: operation temps to 125 °C; low contact resistance
7	MOSFET	Power conversion	650V X2-Class, 650V X3-Class	High power density; easy to mount; space-saving	Ultra-low on-resistance R _{DS} ; high current handling capability; fast body diode





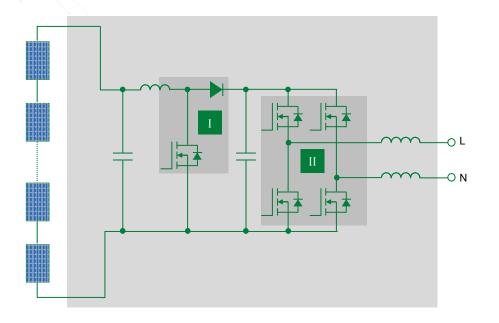
String inverter using high-frequency transformer



	Technology	Product series
	MOSFET	X2-Class, X3-Class
I	SiC Schottky Diode	650V Diodes
	NTC	<u>RA, RB, KR</u>
	MOSFET or	X2-Class, X3-Class
II	IGBT	650 V Trench
III	SiC Schottky Diode	650V Diodes
137	MOSFET or	X2-Class, X3-Class
IV	IGBT	650 V Trench
	MOV	TMOV, UltraMOV, LA
V	GDT	CG3/CG4
	Fuse	Class J, Class RK5, KLKD
171	Gate Driver	IXD_6xxSI, IX4351NE
VI	TVS Diode	<u>SMBJ</u>
VII	TVS Diode Array	<u>SP3130, SP712, SM712</u> <u>SP2555NUTG</u>
	Switch	7000, <u>KSC</u> , <u>ES</u> , <u>KSR</u>
VIII	MOSFET	X2-Class, X3-Class

Transformerless topology for string inverters-Full bridge + MPPT (Boost)



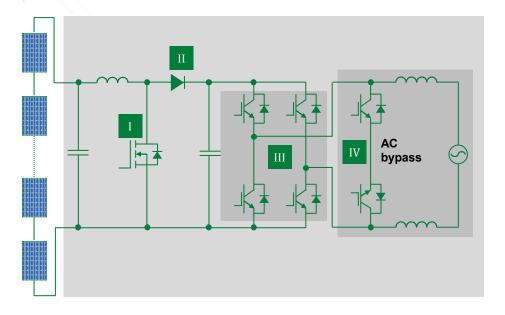


	Technology	Product series
	MOSFET	650V X2-Class, 650V X3-Class
I	SiC Schottky Diode	650V Diodes
	NTC	RA, RB, KR
	MOSFET or	650V X2-Class, 650V X3-Class
II	IGBT	650 V Trench



Transformerless topology for string inverters-HERIC Topology + Boost (MPPT)



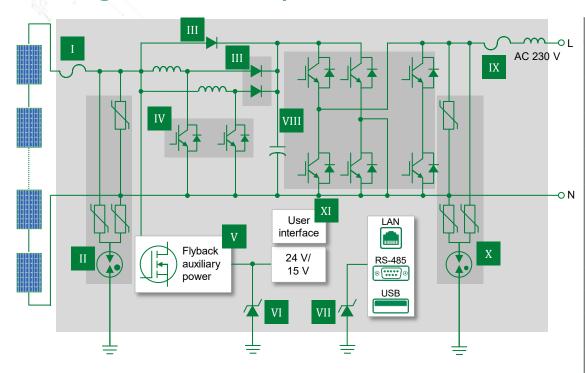


	Technology	Product series
ı	MOSFET or	650V X2-Class, 650V X3-Class
1	IGBT	650 V Trench
II	SiC Schottky Diode	650V Diodes
III	IGBT	650 V Trench
IV	IGBT	650 V Trench



Transformerless topology for string inverters-(<10 kW, MPPT + HERIC)

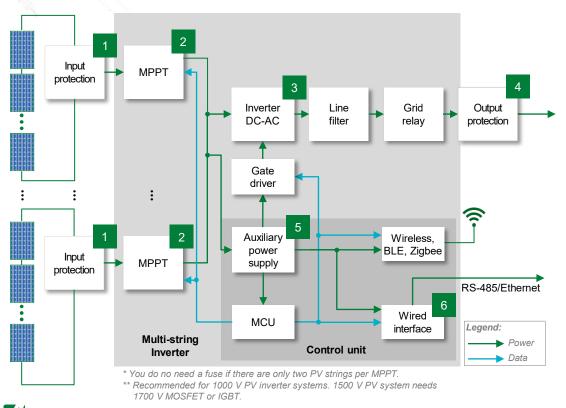




	Technology	Product series
,	Fuse	SPFJ/SPF/SPFI
I	Fuse Block	<u>LPHV</u>
Ш	MOV	<u>Xtreme</u>
11	GDT	<u>CG3/CG4</u>
III -	Rectifier Diode	DSP/DSI/DLA
1111	Fast Recovery Diode	<u>DSEI/DSEP</u>
IV	IGBT	<u>XPT</u>
10	Gate Driver	IXDN602SIATR
	SIC MOSFET	LSIC1MO170E0750
V	Si MOSFET	High Voltage Series, 1200/1500V Polar/HV
	IGBT	IXG*N170(A)
	Gate Driver	<u>IX4427</u>
VI	TVS Diode Array	SM15-02HTG, SM712
VII	TVS Diode Array	SMBJ18CA, SMBJ30CA
1 /111	IGBT	XPT
VIII	Gate Driver	IXDN602SIATR
IX	Fuse	<u>215/324</u>
v	MOV	M3/Xtreme
X	GDT	CG/CG2
ΧI	Switch	7000, KSC, ES, KSR



Multi-string inverter block diagram



Expertise Applied | Answers Delivered

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	Technology	Product series			
	Fuse*	SPF, SPFI, SPXV, SPXI			
1	SPD	SPD2 PV			
	SiC MOSFET or	LSIC1MO120E0120			
2	MOSFET**	High Voltage Series			
	SiC Diode**	<u>1200 V Diode</u>			
	IGBT Module	MIXA, MIXG			
3	Fuse	<u>L75QS</u>			
	TVS Diode	<u>SMBJ</u>			
	Fuse	Class T, Class J			
4	MOV or SPD	UltraMOV, LA, SM7 SPD type 2			
	GDT	<u>CG3/CG4</u>			
_	SIC MOSFET or MOSFET	LSIC1MO170E1000, High Voltage Series, 1200/1500V Polar/HV			
5	Gate Driver	<u>IX4351NE</u>			
	TVS Diode	SMF			
6	TVS Diode Array	<u>SP712, SM712</u> <u>SP2555NUTG</u>			
	Switch	7000, KSC, ES, KSR			

Recommended



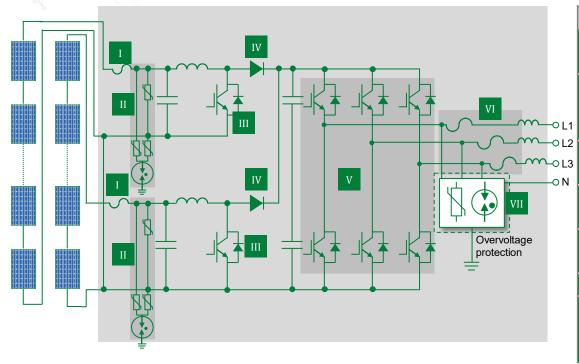
Littelfuse products for multi-string inverters

	Technology	Function in application	Series	Benefits	Features		
1	Fuse	Protects PV modules and conductors from reverse overcurrent conditions	SPF, SPFI, SPXV, SPXI	Prevents power generation losses due to nuisance tripping from changes in temperature	Meets UL and IEC standards; 1000 VDC, 1–30 A ratings available; max interrupt rating 50 kA		
	SPD	Provides equipment protection from transient overvoltage events	SPD2 PV	Withstands high-energy transients to prevent disruption, downtime, and degradation of equipment	Available in 1100 and 1500 Vdc; compact footprint; capability to clamp and withstand transients		
	SiC MOSFET or	Boost converter for high-frequency	LSIC1MO120E0120	Optimized for high-frequency applications	Ultra-low output capacitance and on-resistance		
2	MOSFET*		High Voltage Series	High power density; easy to mount; space-saving	Fast switching time; ultra-low R _{DS(on)}		
	SiC Diode	switching	1200 V Diode	Reduces switching losses; increases system efficiency, reliability, and thermal management	High surge capability; negligible reverse recovery current; Tj 175 °C		
	IGBT Module	IGBT Module Switches power supplies		Allows flow power consumption and fast response	Rugged design with thin wafer technology; low gate charge; low EMI and competitive low $V_{\text{CE}(SAT)}$		
3	Fuse	Protects semiconductor devices in inverter	<u>L75QS</u>	Lower I ² t performance allows for quick response to protect devices from higher heat energy	750 VDC, 35-800 A; interrupt rating DC: 50 kA		
	TVS Diode	Protects IGBTs from transient overload event	<u>SMBJ</u>	Enables compact design; improves system reliability	600 W peak pulse power capability; excellent clamping capability; small footprint		
	Fuse	Overcurrent or short circuit protection	Class T, Class J	Reduces damage to equipment caused by heating and magnetic effects of short-circuit currents	Extremely current-limiting; small footprint; 200 kA interrupting rating		
4	MOV or SPD	Protects from power fluctuations or surges	UltraMOV, LA, SM7 SPD type 2	Withstands high-energy transients to prevent disruption, downtime, degradation of equipment	20 kA nominal interrupting rating and 50 kA maximum interrupting rating		
	GDT	Protects from voltage transients and lightning	CG3/CG4	Small form-factor allows for compact system design; enables product to comply with IEC/UL standards	High energy absorption capability; small form-factor; low leakage current		
	SiC MOSFET or MOSFET High-frequency switching		LSIC1MO170E1000, High Voltage Series, 1200/1500V Polar/HV	Optimized for high frequency; high-power density; easy to mount; space-saving	extremely low gate charge and output capacitance; ultra low on-resistance; fast switching time		
5	Gate Driver	To drive SiC MOSFETs and high-power IGBTs	<u>IX4351NE</u>	Eliminates the need for separate negative supply, quick turn-on and turn-off of power SiC MOSFET	Separate 9 A peak source and sink outputs; internal negative charge pump regulator improved dV/dl immunity and faster turn-off		
	TVS Diode	Protects SiC MOSFET from voltage transients	<u>SMF</u>	Enables compact design; improves system reliability	200 W peak pulse power capability; excellent clamping capability; low profile		
6	TVS Diode Array	Protection of data lines from ESD/EFT and surge events	<u>SP712, SM712</u> <u>SP2555NUTG</u>	Minimizes signal distortion, reduces voltage overshoot, and provides a simplified PCB design	Low capacitance of 2.5 pF; low leakage current of 0.1 μ A; small form factor		
	Switch	On/Off/Reset switch	7000, KSC, ES, KSR	Micro miniature; long life; and low voltage; low power and performance; low voltage leakage	IP 67 Sealing; Au plating: operation temps to 125 °C; low contact resistance		



Multistring inverters for commercial buildings-multiple boost + 2 Level

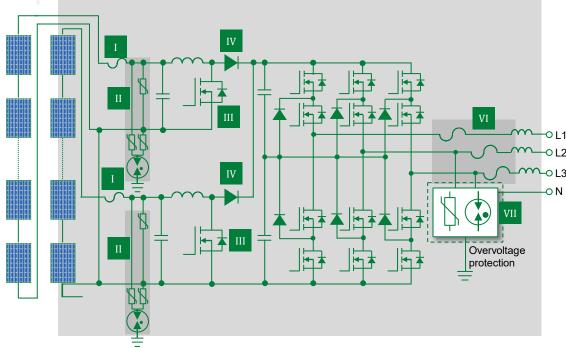




Technology	Product series
Fuse	<u>SPF, SPFI</u>
Fuse Block	<u>LPHV</u>
MOV	<u>UltraMOV/Xtreme</u>
GDT	CG2/CG3
SPD	SPD2 PV
IGBT	<u>XPT</u>
Gate Driver	IXDN602SIATR
Rectifier Diode	DSP/DSI/DLA
Fast Recovery Diode	DSEI/DSEP
IGBT	<u>IXG*N170(A)</u>
Gate Driver	IXDN604SIA
Fuse	Class T/ Class J
MOV	<u>UltraMOV/Xtreme</u>
GDT	CG2/CG3
SPD	SPD2 PV
	Fuse Fuse Block MOV GDT SPD IGBT Gate Driver Rectifier Diode Fast Recovery Diode IGBT Gate Driver Fuse MOV GDT



Multistring inverters for commercial buildings-multiple boost + 3 Level



	Technology	Product series
	Fuse	SPF, SPFI
I	Fuse Block	<u>LPHV</u>
	MOV	<u>UltraMOV/Xtreme</u>
II	GDT	CG2/CG3
	SPD	SPD2 PV
	IGBT	XPT
III	MOSFET	X Class
	Gate Driver	IXDN602SIATR
137	Rectifier Diode	DSP/DSI/DLA
IV	Fast Recovery Diode	DSEI/DSEP
	SIC MOSFET	LSIC1MO170E0750
V	HV IGBT	<u>IXG*N170(A)</u>
	Gate Driver	IXDN604SIA
VI	Fuse	Class T/ Class J
	MOV	<u>UltraMOV/Xtreme</u>
VII	GDT	CG2/CG3
	SPD	SPD2 PV



Safety standards for residential solar installations

	Standard	Title	Market
Ε	IEC 60364-1	Low-Voltage Electrical Installations - Part 1: Fundamental principles, assessment of general characteristics, definitions	Global
/ syste	IEC 60364-7-712	Low-Voltage Electrical Installations - Part 7-712: Requirements for special installations or locations - Solar photovoltaic (PV) power supply systems	Global
_ ₹	NFPA 70	National Electrical Code - Article 690 Solar Photovoltaic (PV) Systems	US



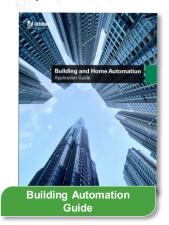
Safety standards for residential solar installations

	Standard	Title	ос	ov	Breaker & Switch	Relay	Power Semi	Market
inverters	IEC 61683	Photovoltaic systems - Power conditioners - Procedure for measuring efficiency					•	Global
	IEC/UL 62109-1	Safety of Power Converters for Use in Photovoltaic Power Systems - Part 1: General requirements	•	•	•	•	•	Global and US
	IEC/UL 62109-2	Safety of Power Converters for Use in Photovoltaic Power Systems - Part 2: Particular requirements for inverters.	•	•	•	•	•	Global and US
	IEC 60269-6	Low-Voltage Fuses - Part 6: Supplementary requirements for fuse-links for the protection of solar photovoltaic energy systems.	•					Global
	IEC 61643-31	Low-voltage surge protective devices – Part 31: Requirements and test methods for SPDs for photovoltaic installations.		•				Global
	UL 1741	Inverters, Converters, Controllers and Interconnection System Equipment for Use With Distributed Energy Resources.	•	•	•	•	•	US
	UL 1449	Surge Protective Devices		•				US
≥	UL 4248-19	Fuseholders - Part 19: Photovoltaic	•					US
	UL 1699B	Photovoltaic (PV) DC Arc-Fault Circuit Protection				•		US
	UL 489B	Molded-Case Circuit Breakers, Molded-Case Switches, and Circuit- Breaker Enclosures for Use with Photovoltaic (PV) Systems.			•			US
	IEEE 1547	IEEE Standard for Interconnection and Interoperability of Distributed Energy Resources with Associated Electric Power Systems Interfaces.						Global
	IEEE 1547.1	IEEE Standard Conformance Test Procedures for Equipment Interconnecting Distributed Energy Resources with Electric Power Systems and Associated Interfaces.						Global



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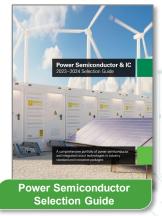


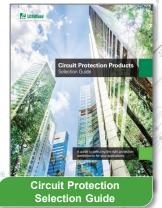














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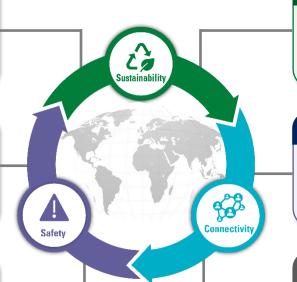
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